



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
100V	80mΩ@10V	3.5A

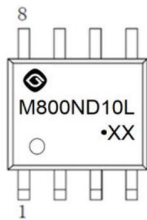
#### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge

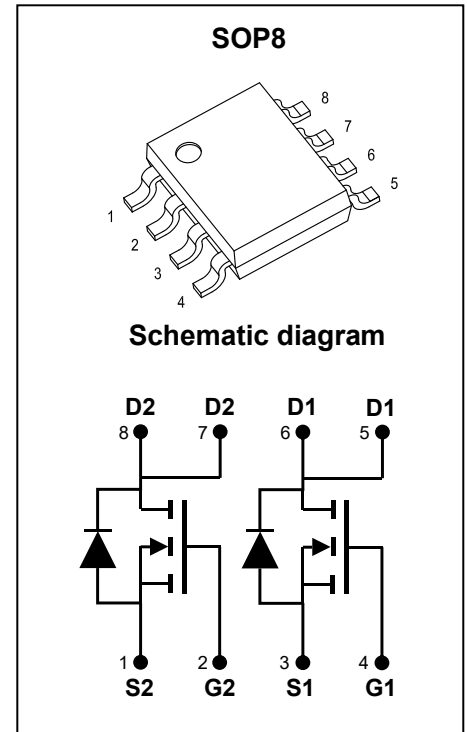
#### Application

- Load Switch
- DC/DC Converter

#### MARKING:



M800ND10L= Device Code  
XX = Date Code  
Soild Dot = Green Device



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	100	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1,5</sup>	$I_D$	3.5	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	14	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	12.3	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	40	mJ
Power Dissipation <sup>5</sup>	$P_D$	1.5	W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	85	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

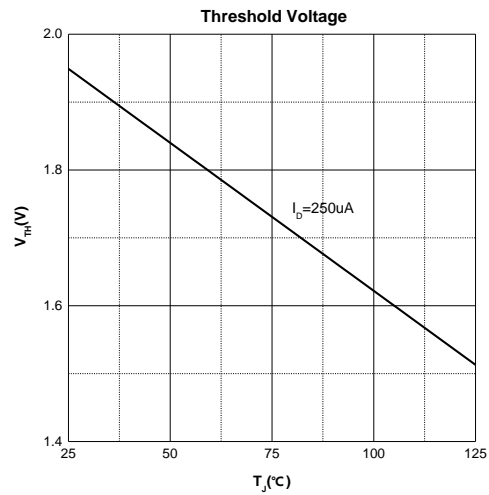
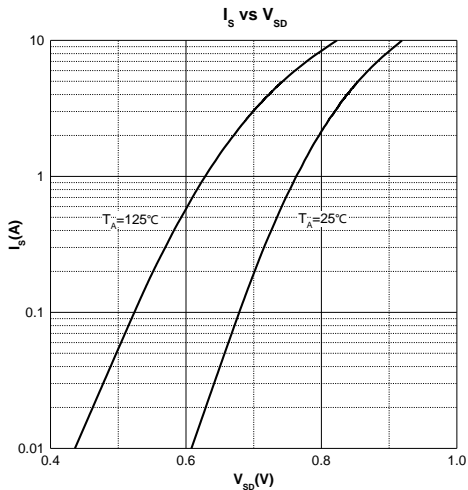
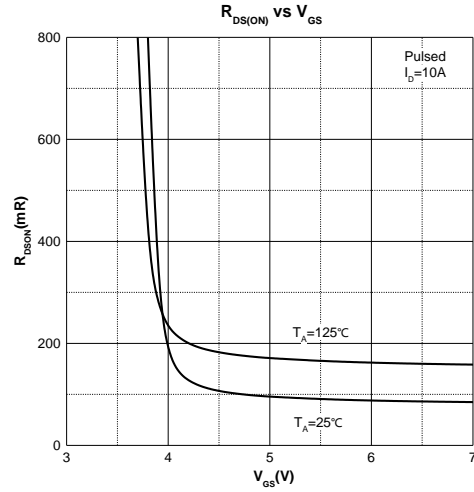
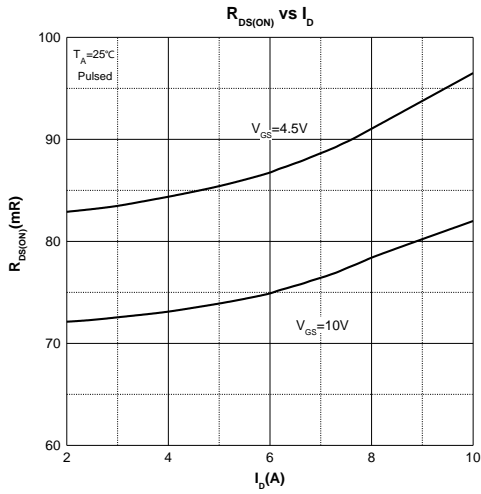
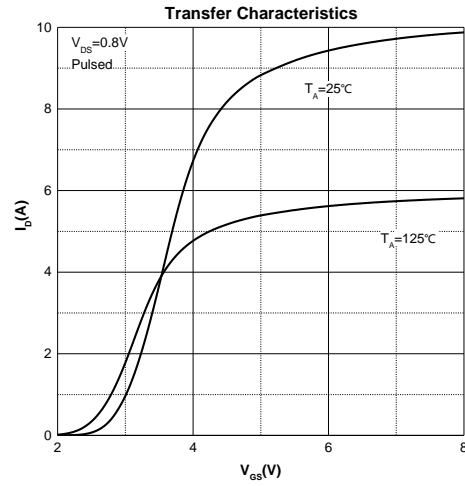
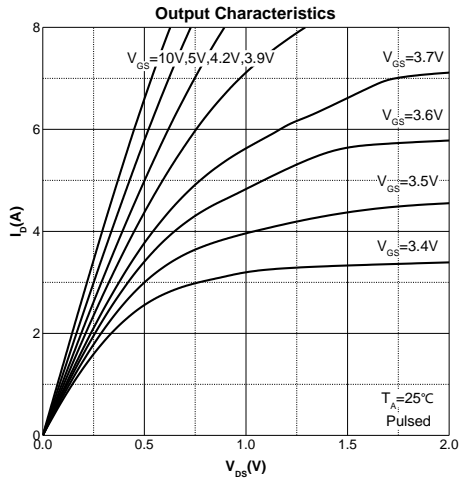
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		80	90	m $\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		847		pF
Output Capacitance	$C_{oss}$			33		
Reverse Transfer Capacitance	$C_{rss}$			29		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.34		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V, I_D = 10A$		19.3		nC
Gate-source Charge	$Q_{gs}$			1.8		
Gate-drain Charge	$Q_{gd}$			4.0		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V,$ $R_L = 15\Omega, R_G = 2.5\Omega$		11		ns
Turn-on Rise Time	$t_r$			7		
Turn-off Delay Time	$t_{d(off)}$			34		
Turn-off Fall Time	$t_f$			9		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.2	V

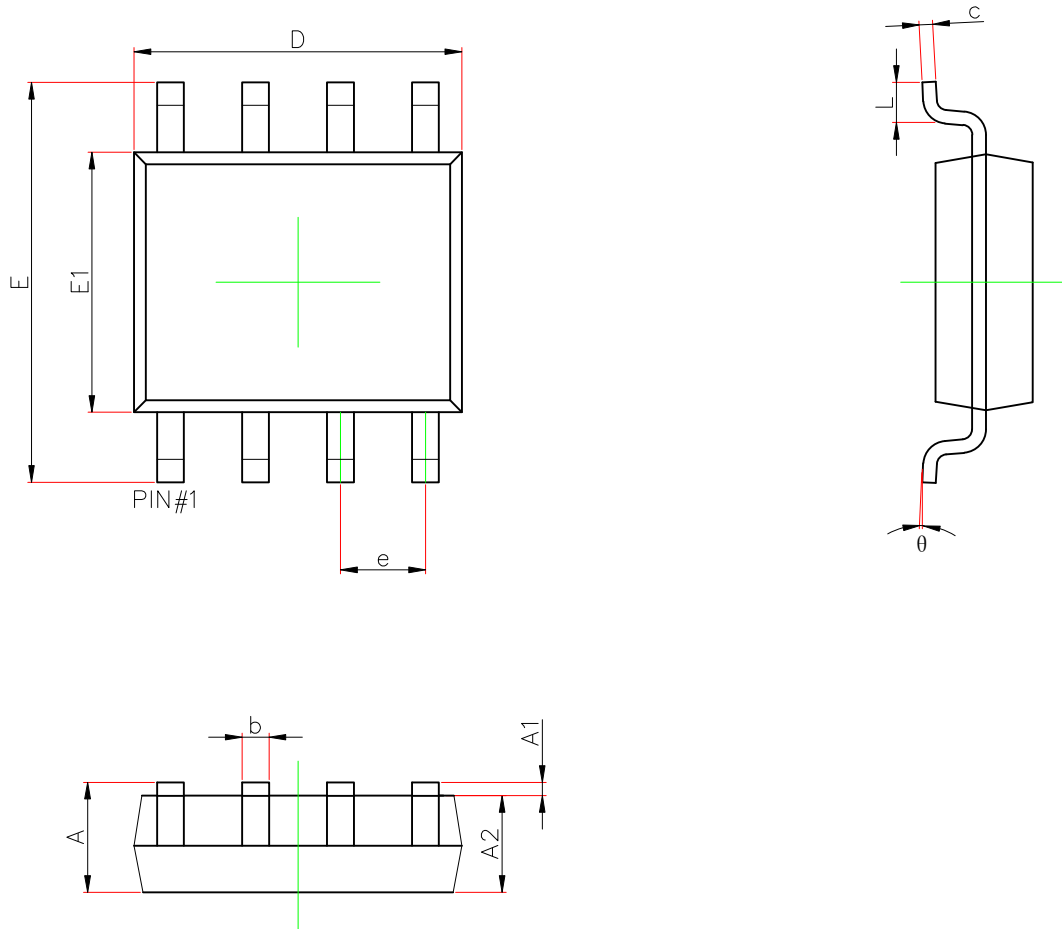
### Notes :

1. The maximum current rating is limited by package. And device mounted on a large heatsink
2. Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
3. EAS condition:  $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ . And device mounted on a large heatsink
6. Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
$\theta$	0°	8°	0°	8°